

Supplementary Information

Investigation of Transcription Factor-DNA Binding with Electrolyte-Gated Organic Transistors

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1. EGOT key performances indicators reproducibility and stability.

g_m (μS)	V_{TH} (V)
2.83 ± 0.54	-0.595 ± 0.022

Table S1 EGOT KPIs. Transconductance (g_m) and threshold voltage (V_{TH}) obtained from the mean of transfer curves of 6 devices with functionalized gate, reported with SEM error.

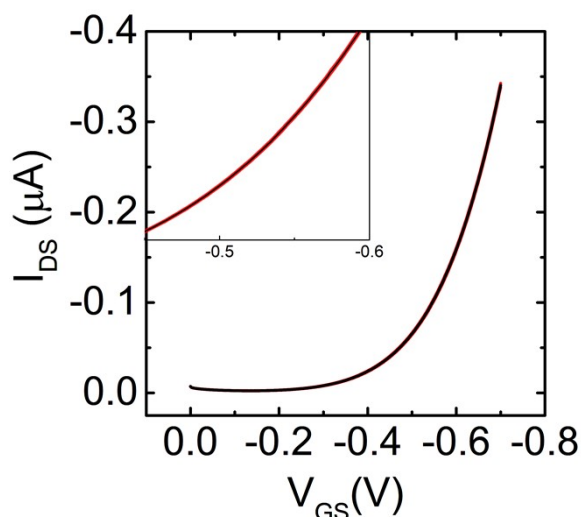


Fig. S1 Example of stability of EGOTs current upon cycling of 20 minutes reported with SEM error (red halo) obtained with the last 8 curves measured. In the inset is shown a zoom of the transfer curve in the range between -0.45 to -0.6 V.

2. Functionalization of the gate electrode: EIS fitting results.

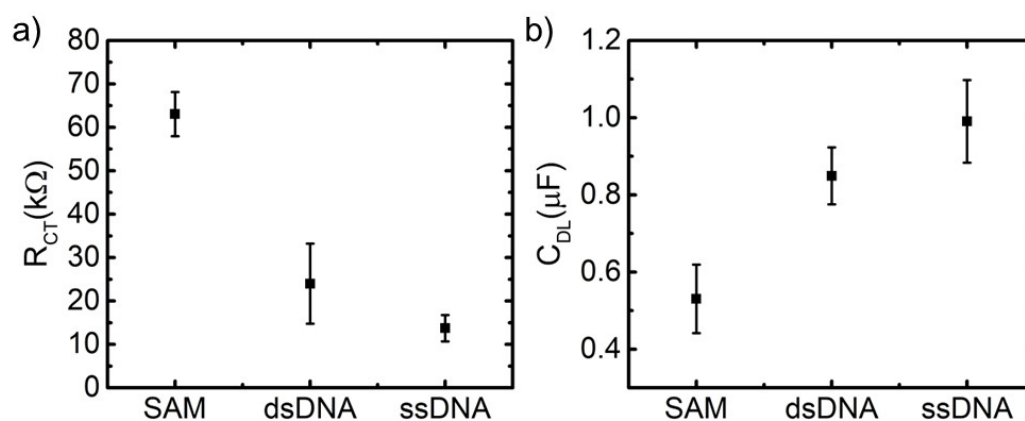


Fig. S2 Results of the fitting of the Nyquist plot shown in figure 2 of the main text with a Randles circuit, showing the a) resistance to charge transfer and the double layer capacitance of the functionalization steps. Error Bars are the standard error of the mean obtained from 3 datasets.